Citations for Ion : Sb

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1964	Sidenius, G. **'Measurement of dE/dX in Gases with Low Energy Heavy Particles'** ***M. R. C. Mcdowell (Ed.)Atomic Collision Processes, North-Holland, Amsterdam, P.709-16 (1964)*** *Comment : S. (20-50 keV) Cl, Ga, Zr, Sb, Pb, Fe, Ca, Ge, U -> H2*	**1964-Side**
1966	Bower, R. W. Baron, R. Mayer, J. W. Marsh, O. J. **'Deep (1-10 micrometer) Penetration of Ion-Implanted Donors in Silicon'** ***Appl. Phys. Letters, 9, 203-05 (1966)*** *Comment : R, dR. 20 keV Sb -> Si (Cryst.)*	**1966-Bowe**
1967	Erikson, L. Davies, J. A. Jespersgaard, P. **'Range Measurements in Oriented Tungsten Single Crystals (0.1-1.0 MeV). Part I: Electronic and Nuclear Stopping Powers.'** ***Phys. Rev., 161, 219-34 (1967)*** *Comment : R, dR. (0.1-1.0 MeV) Na, P, K, Cr, Cu, Br, Kr, Rb, Sb, Xe, W, Rn -> W (Cryst.); (40-500 keV) Na, K, Kr, Xe -> Al (Cryst.)*	**1967-Erik2**
1969	Bottiger, J. Bason, F. **'Energy Loss of Heavy Ions Along Low-Index Directions in Gold Single Crystals'** ***Rad. Effects, 2, 105-10 (1969)*** *Comment : S. (300-970 keV) N, Ne, Na, Mg, S, Cl, Ar, K, Si, Mn, Fe, Kr, Y, Mo, Ag, Cd, Sb, Xe -> Au*	**1969-Bott**
1970	Gamo, K. Masuda, K. Namba, S. Ishihara, S. Itsuro, K. **'Enhanced Diffusion of High-Temperature Ion-Implanted Antimony into Silicon'** ***Appl. Phys. Letters, 17, 391-393 (1970)*** *Comment : R. 20 keV Sb -> Si*	**1970-Gamo**
1970	Nelson, R. S. Cairns, J. A. **'Antimony Implanted Silicon: a Comparison Between the Total Implanted Concentration Profile and the Donor Concentration Profile'** ***Rad. Effects, 6, 131-34 (1970)*** *Comment : R, dR. 100 keV Sb -> Si*	**1970-Nels**
1971	Crowder, B. L. **'The Influence of the Amorphous Phase on Ion Distributions and Annealing Behavior of Group Iii and Group V Ions Implanted into Silicon'** ***J. Electrochem. Soc., 118, 943-52 (1971)*** *Comment : R,dR. (50-300 keV) B, Al Ga, P, As, Sb, Bi -> Si*	**1971-Crow**
1971	Gamo, K. Iwaki, M. Masuda, K. Namba, S. Ishihara, S. **'Enhanced Diffusion and Electrical Properties of Ion Implanted Silicon'** ***Intl. Conf. Ion Implantation in Semiconductors, Ed. by I. Ruge and J. Graul, 459-465 (1971)*** *Comment : R. 20-50 keV Sb, In -> Si*	**1971-Gamo2**

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1971	Gamo, K. Iwaki, M. Masuda, K. Ishihara, S. Kimura, K. **'Concentration Profiles of Ion Implanted Impurities into Silicon'** ***Sci. Pap. Inst. Phys. Chem. Res. (Japan), 65, 19-21 (1971)*** *Comment : R, dR. 20-80 keV In, 20 keV Sb -> Si*	**1971-Gamo3**
1971	Sigurd, D. Domeij, B. **'Critical Angles of Sb and Bi Implanted Si'** ***Phys. Letters, 36A, 81-82 (1971)*** *Comment : R. 40 keV Sb, Bi -> Si ([111], [110], [100])*	**1971-Sigu**
1972	Hart, R. R. Lee, D. H. March, O. J. **'Enhanced Migration of Implanted Sb and In in Si Covered with Evaporated Al'** ***Appl. Phys. Letters, 20, 76-77 (1972)*** *Comment : R. 180 keV Sb, In -> Al, Si*	**1972-Hart**
1973	Gibbons, J. F. Mylroie, S. **'Estimation of Impurity Profiles in Ion-Implanted Amorphous Targets using Joined Half-Gaussian Distributions'** ***Appl. Phys. Letters, 22, 568-569 (1973)*** *Comment : R. 120 keV Sb, 60 keV B -> Si*	**1973-Gibb2**
1974	Drum, C. M. **'Diffusion of Ion Implanted Antimony and Arsenic in Silicon'** ***J. Electrochem. Soc., 121, 93C (1974)*** *Comment : R, dR. Sb, As (30-80 Kev) -> Si*	**1974-Drum**
1975	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. **'Range Parameters of Heavy Ions in Amorphous Targets at LSS-Energies of 0.0006 < Epsilon < 0.3.'** ***Phys. Letters, 55A, 170-172 (1975)*** *Comment : R, dR. 1-60 keV As, Ge, Sb, Au, Bi -> Si, Ge, Al*	**1975-Oetz**
1976	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. **'Range Parameters of Heavy Ions in Silicon and Germanium with Released Energies from 0.01 < epsilon < 10'** ***Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 245-54 (1976)*** *Comment : R, dR. (1-40 keV) Al, Sb, As, Ge, Au, Bi -> Si, Ge*	**1976-Oetz**
1976	Schmidt, K. -H. Wohlfarth, H. Clerc, H. -G. Lang, W. Schrader, H. **'Energy Loss, Energy Straggling and Angular Straggling of Heavy Ions in Carbon Foils'** ***Nucl. Inst. Methods, 134, 157-66 (1976)*** *Comment : S, dS. 80-100 MeV Kr, Rb, Sr, Y, Zr, Nb, Sb, Te -> C*	**1976-Schm**
1977	Bogh, E. Hogild, P. Stensgaard, I. **'Spatial Distribution of Defects in Ion Bombarded Silicon and Germanium'** ***Rad. Effects, 7, 115-121 (1977)*** *Comment : R. 10-400 keV P, Sb -> Si, Ge*	**1977-Bogh**

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1979	Braunstein, G. Bernstein, T. Carsenty, U. Kalish, R. **'Depth Profile of Antimony Implanted into Diamond'** ***J. Appl. Phys., 50, 5731-35 (1979)*** *Comment : R, dR. 350 keV Sb -> Diamond*	**1979-Brau**
1979	Santry, D. C. Werner, R. D. Westcott, O. M. **'The Range of 120 keV Ions in Solids'** ***IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)*** *Comment : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si*	**1979-Sant**
1979	White, C. W. Christie, W. H. Pronko, P. P. Appleton, B. R. Wilson, S. R. **'Dopant Profile Changes Induced by Pulsed Laser Annealing'** ***Rad. Effects, 47, 37-40 (1979)*** *Comment : R, dR. 35-150 keV B, P, As, Sb, Cu, Fe -> Si*	**1979-Whit**
1979	White, C. W. Pronko, P. P. Wilson, S. R. Appleton, B. R. Narayan, J. **'Effects of Pulsed Ruby-Laser Annealing on As and Sb Implanted Silicon'** ***J. Appl. Phys., 50, 3261-3273 (1979)*** *Comment : R, dR. 100 keV 75As, 121Sb -> Si*	**1979-Whit2**
1980	Braunstein, G. Talmi, A. Kalish, R. Bernstein, T. Beserman, R. **'Radiation Damage and Annealing in Sb Implanted Diamond'** ***Rad. Effects, 48, 139-144 (1980)*** *Comment : R, dR. 350 keV Sb -> C*	**1980-Brau**
1980	Chu, W. K. Kastl, R. H. Murley, P. C. **'Low-Energy Antimony Implantation in Silicon'** ***Rad. Effects, 47, 1-6 (1980)*** *Comment : R, dR. 5-60 keV Sb -> Si*	**1980-Chu**
1980	Kalbitzer, S. Oetzmann, H. **'Ranges and Range Theories'** ***Rad. Effects, 47, 57-72, (1980)*** *Comment : R, dR. .1-2 MeV Bi, Sb, As, Ge, P, Au, Cs, Eu, Gd Tb -> Si, Ge, C, Al*	**1980-Kalb**
1980	Schmitt, A. Schorer, G. **'Damage Anneal of Antimony/Phosphorus Double Implants in Silicon'** ***Appl. Phys., 22, 137-143 (1980)*** *Comment : R, dR. 200 keV Sb -> Si*	**1980-Schm**
1980	Sugiura, H. **'Silicon Molecular Beam Epitaxy with Antimony Ion Doping'** ***J. Appl. Phys., 51, 2630-2633 (1980)*** *Comment : R, dR. 130-1000 eV Sb -> Si*	**1980-Sugi**

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1980	Wampler, W. R. Follstaedt, D. M. Picraux, S. T. **'Electron Beam Annealing of Ion Implanted Al'** ***Appl. Phys. Letters, 36, 366-368 (1980)*** *Comment : R, dR. 150 keV Zn Sb -> Al*	**1980-Wamp**
1985	Ingrahm, D. C. Baker, J. A. Walsh, D. A. **'Range Distributions of MeV Implants in Silicon'** ***Nucl. Inst. Methods, B7/8, 361-365 (1985)*** *Comment : R, dR. B, P, Sb (0.4-6 MeV) -> Si*	**1985-Ingr**
1986	Geyer, E. Reschke, D. Freitag, K. **'Z1 Stopping Power Oscillation in the Nuclear Stopping Regime as Obtained by Time-of-Flight Spectroscopy of Heavy Ions in Hydrogen'** ***Nucl. Inst. Methods, B15, 81-85 (1986)*** *Comment : S. Heavy Ions (49-65) at 26 - 90 keV -> H2 (gas)*	**1986-Geye**
1987	Freitag, K. Reschke, D. Geyer, E. **'Stopping Power Measurements for Low Energy Ions in Gases by Time-of-Flight Spectroscopy'** ***Nucl. Inst. Methods, B27, 344-352 (1987)*** *Comment : S. Heavy Ions (49-65) at 27 - 90 keV -> H2 (gas)*	**1987-Frei**